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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SIO, SSU, UART/USART
Peripherals	LCD, POR, PWM, Voltage Detect, WDT
Number of I/O	72
Program Memory Size	48KB (48K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	3.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f2la87anfa-v0

Table 1.2 Programmable I/O Ports Provided for Each Group (R8C/LA3A Group, R8C/LA5A Group)

Programmable I/O Port	R8C/LA3A Group Total: 26 I/O pins								R8C/LA5A Group Total: 44 I/O pins							
	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
P0	—	—	—	—	—	—	—	—	✓	✓	✓	✓	✓	✓	✓	✓
P2	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P3	—	—	—	—	—	—	—	—	✓	✓	✓	✓	✓	✓	✓	✓
P5	—	✓	✓	✓	✓	✓	✓	✓	—	✓	✓	✓	✓	✓	✓	✓
P7	—	—	—	—	—	—	✓	—	—	—	—	—	—	✓	✓	✓
P8	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P9	—	—	—	—	—	—	✓	✓	—	—	—	—	—	—	✓	✓

Notes:

1. The symbol “✓” indicates a programmable I/O port.
2. The symbol “—” indicates the settings should be made as follows:
 - Set 0 to the corresponding bits in the PDi (i = 0, 3, 5, 7, 9) register. When read, the content is 0.
 - Set 0 to the corresponding bits in the Pi (i = 0, 3, 5, 7, 9) register. When read, the content is 0.

Table 1.3 Programmable I/O Ports Provided for Each Group (R8C/LA6A Group, R8C/LA8A Group)

Programmable I/O Port	R8C/LA6A Group Total: 56 I/O pins								R8C/LA8A Group Total: 72 I/O pins							
	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
P0	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P1	✓	✓	✓	✓	✓	✓	—	—	✓	✓	✓	✓	✓	✓	✓	✓
P2	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P3	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P4	✓	✓	—	—	—	—	—	—	✓	✓	✓	✓	✓	✓	✓	✓
P5	—	✓	✓	✓	✓	✓	✓	✓	—	✓	✓	✓	✓	✓	✓	✓
P6	✓	✓	✓	✓	✓	✓	✓	—	✓	✓	✓	✓	✓	✓	✓	✓
P7	—	—	—	—	—	—	—	—	—	✓	✓	✓	✓	✓	✓	✓
P8	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P9	—	—	—	—	—	—	✓	✓	—	—	—	—	—	—	✓	✓

Notes:

1. The symbol “✓” indicates a programmable I/O port.
2. The symbol “—” indicates the settings should be made as follows:
 - Set 0 to the corresponding bits in the PDi (i = 1, 4 to 7, 9) register. When read, the content is 0.
 - Set 0 to the corresponding bits in the Pi (i = 1, 4 to 7, 9) register. When read, the content is 0.
 - Set 0 to the corresponding bits in the P7DRR register. When read, the content is 0.

Table 1.7 Specifications (2)

Item	Function		Specification		
Timer	Timer RB0, Timer RB1		8 bits × 2 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode		
	Timer RC		16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output: 3 pins), PWM2 mode (PWM output: 1 pin)		
	Timer RH		Real-time clock mode (counting of seconds, minutes, hours, day of the week, date, month, year), output compare mode		
	Timer RJ0 Timer RJ1 Timer RJ2	R8C/LA3A Group R8C/LA5A Group R8C/LA6A Group	Timer RJ0, Timer RJ1	16 bits × 2	Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
		R8C/LA8A Group	Timer RJ0, Timer RJ1, Timer RJ2	16 bits × 3	
Serial Interface	UART0		1 channel Clock synchronous serial I/O/UART		
	UART2		1 channel Clock synchronous serial I/O/UART, I ² C mode (I ² C-bus), multiprocessor communication function		
Synchronous Serial Communication Unit (SSU)			1 (shared with I ² C-bus)		
I ² C bus			1 (shared with SSU)		
A/D Converter		R8C/LA3A Group	10-bit resolution × 5 channels, including sample and hold function, with sweep mode, temperature sensor included (measurement temperature range: –20 to 85 °C (N version)/ –40 to 85 °C (D version))		
		R8C/LA5A Group	10-bit resolution × 7 channels, including sample and hold function, with sweep mode, temperature sensor included (measurement temperature range: –20 to 85 °C (N version)/ –40 to 85 °C (D version))		
		R8C/LA6A Group	10-bit resolution × 8 channels, including sample and hold function, with sweep mode, temperature sensor included (measurement temperature range: –20 to 85 °C (N version)/ –40 to 85 °C (D version))		
		R8C/LA8A Group	10-bit resolution × 12 channels, including sample and hold function, with sweep mode, temperature sensor included (measurement temperature range: –20 to 85 °C (N version)/ –40 to 85 °C (D version))		
Comparator B		R8C/LA3A Group	1 circuit (comparator B1)		
		R8C/LA5A Group R8C/LA6A Group R8C/LA8A Group	2 circuits (comparator B1, comparator B3)		

Table 1.21 Pin Functions for R8C/LA8A Group (2)

Item	Pin Name	I/O Type	Description
I ² C bus	SCL	I/O	Clock I/O pin.
	SDA	I/O	Data I/O pin.
SSU	SSI	I/O	Data I/O pin.
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin.
	SSCK	I/O	Clock I/O pin.
	SSO	I/O	Data I/O pin.
Reference voltage input	VREF	I	Reference voltage input pin for the A/D converter.
A/D converter	AN0 to AN11	I	A/D converter analog input pins.
	$\overline{\text{ADTRG}}$	I	AD external trigger input pin.
Comparator B	IVCMP1, IVCMP3	I	Comparator B analog voltage input pins.
	IVREF1, IVREF3	I	Comparator B reference voltage input pins.
I/O ports	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_6, P6_0 to P6_7, P7_0 to P7_6, P8_0 to P8_7, P9_0, P9_1	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. Ports P7_0, P7_1 and P8 can be used as LED drive ports.
Segment output	SEG0 to SEG39	O	LCD segment output pins.
Common output	COM0 to COM3, COMEXP	O	LCD common output pins.
LCD power supply	VL1	I	Apply the following voltage: $1\text{ V} \leq \text{VL1} \leq \text{VCC}$ and $\text{VL1} \leq \text{VL2}$.
	VL2	I	Apply the following voltage: $\text{VL2} \leq 5.5\text{ V}$ and $\text{VL1} \leq \text{VL2} \leq \text{VL3}$.
	VL3	I	Apply the following voltage: $\text{VL3} \leq 5.5\text{ V}$ and $\text{VL2} \leq \text{VL3}$.

I: Input O: Output I/O: Input and output

Note:

1. Contact the oscillator manufacturer for oscillation characteristics.

3. Memory

Figure 3.1 shows a Memory Map of each group. Each group has a 1-Mbyte address space from addresses 00000h to FFFFFh. For example, a 48-Kbyte internal ROM area is allocated addresses 04000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.

The internal ROM (data flash) is allocated higher addresses, beginning with address 03000h.

For example, two 1-Kbyte internal ROM (data flash) areas are allocated addresses 03000h to 037FFh. Two 2-Kbyte internal RAM (data flash) areas are allocated addresses 03000h to 03FFFh.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 3.5-Kbyte internal RAM area is allocated addresses 00400h to 011FFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh. Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.

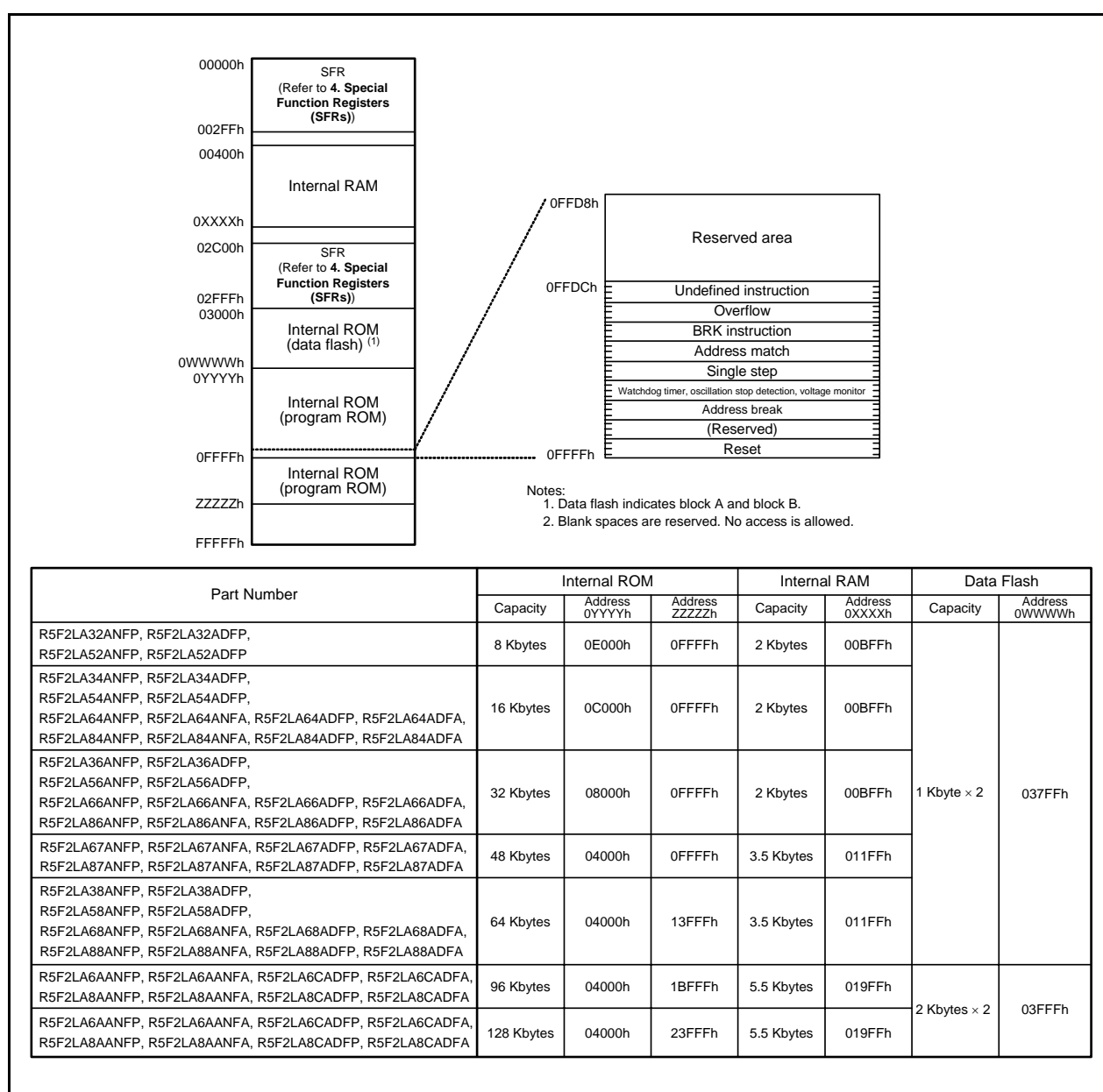


Figure 3.1 Memory Map

Table 4.12 SFR Information for R8C/LA8A Group (3) ⁽¹⁾

Address	Register	Symbol	After Reset
0080h	Timer RJ0 Control Register	TRJ0CR	00h
0081h	Timer RJ0 I/O Control Register	TRJ0IOC	00h
0082h	Timer RJ0 Mode Register	TRJ0MR	00h
0083h	Timer RJ0 Event Pin Select Register	TRJ0ISR	00h
0084h	Timer RJ0 Register	TRJ0	FFh
0085h			FFh
0086h			
0087h			
0088h	Timer RJ1 Control Register	TRJ1CR	00h
0089h	Timer RJ1 I/O Control Register	TRJ1IOC	00h
008Ah	Timer RJ1 Mode Register	TRJ1MR	00h
008Bh	Timer RJ1 Event Pin Select Register	TRJ1ISR	00h
008Ch	Timer RJ1 Register	TRJ1	FFh
008Dh			FFh
008Eh			
008Fh			
0090h	Timer RJ2 Control Register	TRJ2CR	00h
0091h	Timer RJ2 I/O Control Register	TRJ2IOC	00h
0092h	Timer RJ2 Mode Register	TRJ2MR	00h
0093h	Timer RJ2 Event Pin Select Register	TRJ2ISR	00h
0094h	Timer RJ2 Register	TRJ2	FFh
0095h			FFh
0096h			
0097h			
0098h	Timer RB1 Control Register	TRB1CR	00h
0099h	Timer RB1 One-Shot Control Register	TRB1OCR	00h
009Ah	Timer RB1 I/O Control Register	TRB1IOC	00h
009Bh	Timer RB1 Mode Register	TRB1MR	00h
009Ch	Timer RB1 Prescaler Register	TRB1PRE	FFh
009Dh	Timer RB1 Secondary Register	TRB1SC	FFh
009Eh	Timer RB1 Primary Register	TRB1PR	FFh
009Fh			
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h	UART2 Transmit/Receive Mode Register	U2MR	00h
00A9h	UART2 Bit Rate Register	U2BRG	XXh
00AAh	UART2 Transmit Buffer Register	U2TB	XXh
00ABh			XXh
00ACh	UART2 Transmit/Receive Control Register 0	U2C0	00001000b
00ADh	UART2 Transmit/Receive Control Register 1	U2C1	00000010b
00AEh	UART2 Receive Buffer Register	U2RB	XXh
00AFh			XXh
00B0h	UART2 Digital Filter Function Select Register	URXDF	00h
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h			
00B9h			
00BAh			
00BBh	UART2 Special Mode Register 5	U2SMR5	00h
00BCh	UART2 Special Mode Register 4	U2SMR4	00h
00BDh	UART2 Special Mode Register 3	U2SMR3	000X0X0Xb
00BEh	UART2 Special Mode Register 2	U2SMR2	X0000000b
00BFh	UART2 Special Mode Register	U2SMR	X0000000b

X: Undefined

Note:

- Blank spaces are reserved. No access is allowed.

Table 4.15 SFR Information for R8C/LA8A Group (6) ⁽¹⁾

Address	Register	Symbol	After Reset
0140h			
0141h			
0142h			
0143h			
0144h			
0145h			
0146h			
0147h			
0148h			
0149h			
014Ah			
014Bh			
014Ch			
014Dh			
014Eh			
014Fh			
0150h			
0151h			
0152h			
0153h			
0154h			
0155h			
0156h			
0157h			
0158h			
0159h			
015Ah			
015Bh			
015Ch			
015Dh			
015Eh			
015Fh			
0160h			
0161h			
0162h			
0163h			
0164h			
0165h			
0166h			
0167h			
0168h			
0169h			
016Ah			
016Bh			
016Ch			
016Dh			
016Eh			
016Fh			
0170h			
0171h			
0172h			
0173h			
0174h			
0175h			
0176h			
0177h			
0178h			
0179h			
017Ah			
017Bh			
017Ch			
017Dh			
017Eh			
017Fh			

X: Undefined

Note:

1. Blank spaces are reserved. No access is allowed.

Table 4.18 SFR Information for R8C/LA8A Group (9) (1)

Address	Register	Symbol	After Reset
0200h	LCD Control Register	LCR0	00h
0201h			
0202h	LCD Option Clock Control Register	LCR2	00h
0203h	LCD Clock Control Register	LCR3	00h
0204h	LCD Display Control Register	LCR4	00h
0205h			
0206h	LCD Port Select Register 0	LSE0	00h
0207h	LCD Port Select Register 1	LSE1	00h
0208h	LCD Port Select Register 2	LSE2	00h
0209h	LCD Port Select Register 3	LSE3	00h
020Ah	LCD Port Select Register 4	LSE4	00h
020Bh	LCD Port Select Register 5	LSE5	00h
020Ch			
020Dh			
020Eh			
020Fh			
0210h	LCD Display Data Register	LRA0L	XXh
0211h		LRA1L	XXh
0212h		LRA2L	XXh
0213h		LRA3L	XXh
0214h		LRA4L	XXh
0215h		LRA5L	XXh
0216h		LRA6L	XXh
0217h		LRA7L	XXh
0218h		LRA8L	XXh
0219h		LRA9L	XXh
021Ah		LRA10L	XXh
021Bh		LRA11L	XXh
021Ch		LRA12L	XXh
021Dh		LRA13L	XXh
021Eh		LRA14L	XXh
021Fh		LRA15L	XXh
0220h		LRA16L	XXh
0221h		LRA17L	XXh
0222h		LRA18L	XXh
0223h		LRA19L	XXh
0224h		LRA20L	XXh
0225h		LRA21L	XXh
0226h		LRA22L	XXh
0227h		LRA23L	XXh
0228h		LRA24L	XXh
0229h		LRA25L	XXh
022Ah		LRA26L	XXh
022Bh		LRA27L	XXh
022Ch		LRA28L	XXh
022Dh		LRA29L	XXh
022Eh		LRA30L	XXh
022Fh		LRA31L	XXh
0230h		LRA32L	XXh
0231h		LRA33L	XXh
0232h		LRA34L	XXh
0233h		LRA35L	XXh
0234h		LRA36L	XXh
0235h		LRA37L	XXh
0236h		LRA38L	XXh
0237h		LRA39L	XXh
:			
2FFFh			

X: Undefined

Note:

- Blank spaces are reserved. No access is allowed.

Table 5.7 Flash Memory (Program ROM) Characteristics
(VCC = 1.8 to 5.5 V and T_{opr} = 0 to 60 °C, unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance ⁽¹⁾		10,000 ⁽²⁾	—	—	times
—	Byte program time		—	80	—	μs
—	Block erase time		—	0.12	—	s
t _d (SR-SUS)	Time delay from suspend request until suspend		—	—	0.25 + CPU clock × 3 cycles	ms
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		—	—	30 + CPU clock × 1 cycle	μs
—	Program, erase voltage		1.8	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time ⁽⁶⁾	Ambient temperature = 85 °C	10	—	—	year

Notes:

- Definition of programming/erasure endurance
 The programming and erasure endurance is defined on a per-block basis.
 If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
 However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
- Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
- In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
- If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
- Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
- The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.8 Flash Memory (Data flash Block A and Block B) Characteristics
(V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance ⁽¹⁾		10,000 (2)	–	–	time s
–	Byte program time (program/erase endurance ≤ 10,000 times)		–	150	–	μs
–	Block erase time (program/erase endurance ≤ 10,000 times)		–	0.05	1	s
t _d (SR-SUS)	Time delay from suspend request until suspend		–	–	0.25 + CPU clock × 3 cycles	ms
–	Time from suspend until erase restart		–	–	30 + CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		–	–	30 + CPU clock × 1 cycle	μs
–	Program, erase voltage		1.8	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20 ⁽⁶⁾	–	85	°C
–	Data hold time ⁽⁷⁾	Ambient temperature = 85 °C	10	–	–	year

Notes:

- Definition of programming/erasure endurance
 The programming and erasure endurance is defined on a per-block basis.
 If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
 However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
- Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
- In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
- If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
- Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
- 40 °C for D version.
- The data hold time includes time that the power supply is off or the clock is not supplied.

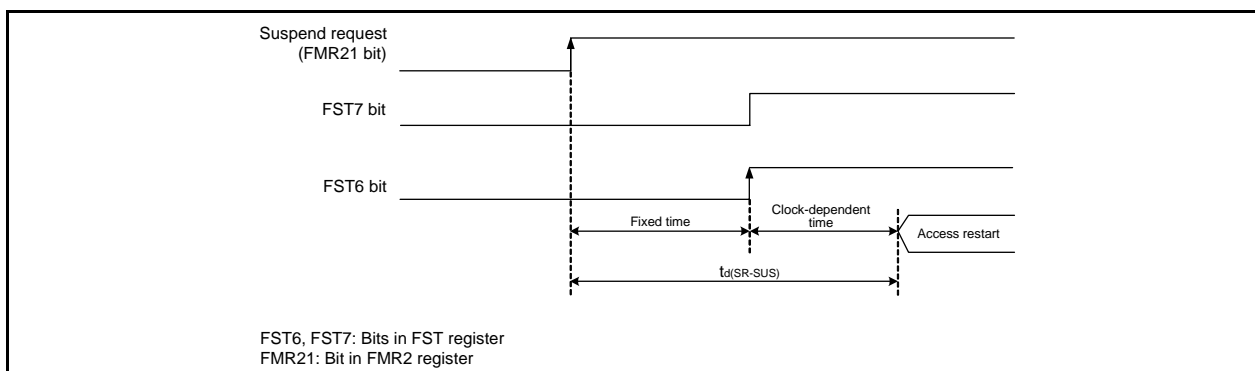


Figure 5.2 Time delay until Suspend

Table 5.23 DC Characteristics (6) [1.8 V ≤ V_{CC} < 2.7 V]**(T_{opr} = −20 to 85 °C (N version)/ −40 to 85 °C (D version), unless otherwise specified.)**

Symbol	Parameter		Condition								Standard			Unit
			Oscillation Circuit		On-Chip Oscillator		CPU Clock	Low-Power-Consumption Setting	Other		Min.	Typ. (3)	Max .	
			XIN (2)	XCIN	High-Speed	Low-Speed								
Icc	Power supply current (1)	High-speed clock mode	8 MHz	Off	Off	125 kHz	No division	—		—	2.1	—	mA	
			8 MHz	Off	Off	125 kHz	Divide-by-8	—		—	0.9	—	mA	
		High-speed on-chip oscillator mode	Off	Off	5 MHz	125 kHz	No division	—		—	1.8	5	mA	
			Off	Off	5 MHz	125 kHz	Divide-by-8	—		—	1.1	—	mA	
			Off	Off	4 MHz	125 kHz	Divide-by-16	MSTCR0 = BEh MSTCR1 = 3Fh		—	0.9	—	mA	
		Low-speed on-chip oscillator mode	Off	Off	Off	125 kHz	No division	FMR27 = 1 VCA20 = 0		—	106	300	μA	
			Off	Off	Off	125 kHz	Divide-by-8	FMR27 = 1 VCA20 = 0		—	54	200	μA	
		Low-speed clock mode	Off	32 kHz	Off	Off	No division	FMR27 = 1 VCA20 = 0		—	54	200	μA	
			Off	32 kHz	Off	Off	No division	FMSTP = 1 VCA20 = 0	Flash memory off Program operation on RAM	—	36	—	μA	
		Wait mode	Off	Off	Off	125 kHz	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1	While a WAIT instruction is executed Peripheral clock operation	—	9.0	50	μA	
			Off	Off	Off	125 kHz	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off	—	2.5	31	μA	
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 0	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode LCD drive control circuit (4) When external division resistors are used	—	2.4	—	μA	
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode	—	1.7	—	μA	
		Stop mode	Off	Off	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Topr = 25 °C Peripheral clock off	—	0.5	2.2	μA	
			Off	Off	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM10 = 1	Topr = 85 °C Peripheral clock off	—	1.2	—	μA	
		Power-off mode	Off	Off	Off	Off	—	—	Power-off 0 Topr = 25 °C	—	0.01	0.1	μA	
			Off	Off	Off	Off	—	—	Power-off 0 Topr = 85 °C	—	0.02	—	μA	
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 25 °C	—	1.2	4	μA	
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 85 °C	—	2	—	μA	

Notes:

1. V_{CC} = 1.8 V to 2.7 V, single chip mode, output pins are open, and other pins are V_{SS}.
2. XIN is set to square wave input.
3. V_{CC} = 2.2 V
4. VLCD = V_{CC}, external division resistors are used for VL3 to VL1, 1/3 bias, 1/4 duty, f(FR) = 64 Hz, SEG0 to SEG26 are selected, and segment and common output pins are open. The standard value does not include the current that flows through external division resistors.

5.1.5 AC Characteristics

Table 5.24 Timing Requirements of Synchronous Serial Communication Unit (SSU)
($V_{CC} = 1.8$ to 5.5 V, $V_{SS} = 0$ V, and $T_{opr} = -20$ to 85 °C (N version)/
 -40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
tsucyc	SSCK clock cycle time			4	—	—	tcyc (1)
tHI	SSCK clock "H" width			0.4	—	0.6	tsucyc
tLO	SSCK clock "L" width			0.4	—	0.6	tsucyc
tRISE	SSCK clock rising time	Master		—	—	1	tcyc (1)
		Slave		—	—	1	μs
tFALL	SSCK clock falling time	Master		—	—	1	tcyc (1)
		Slave		—	—	1	μs
tsu	SSO, SSI data input setup time			100	—	—	ns
tH	SSO, SSI data input hold time			1	—	—	tcyc (1)
tLEAD	\overline{SCS} setup time	Slave		1tcyc + 50	—	—	ns
tLAG	\overline{SCS} hold time	Slave		1tcyc + 50	—	—	ns
tOD	SSO, SSI data output delay time			—	—	1tcyc + 20	ns
tsa	SSI slave access time		$2.7 \text{ V} \leq V_{CC} \leq 5.5 \text{ V}$	—	—	1.5tcyc + 100	ns
			$1.8 \text{ V} \leq V_{CC} < 2.7 \text{ V}$	—	—	1.5tcyc + 200	ns
tor	SSI slave out open time		$2.7 \text{ V} \leq V_{CC} \leq 5.5 \text{ V}$	—	—	1.5tcyc + 100	ns
			$1.8 \text{ V} \leq V_{CC} < 2.7 \text{ V}$	—	—	1.5tcyc + 200	ns

Note:

1. $1tcyc = 1/f_1(s)$

Table 5.25 Timing Requirements of I²C bus Interface ⁽¹⁾
(V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t _{SCL}	SCL input cycle time		12tcyc + 600 ⁽¹⁾	–	–	ns
t _{SCLH}	SCL input “H” width		3tcyc + 300 ⁽¹⁾	–	–	ns
t _{SCLL}	SCL input “L” width		5tcyc + 500 ⁽¹⁾	–	–	ns
t _{sf}	SCL, SDA input fall time		–	–	300	ns
t _{SP}	SCL, SDA input spike pulse rejection time		–	–	1tcyc ⁽¹⁾	ns
t _{BUF}	SDA input bus-free time		5tcyc ⁽¹⁾	–	–	ns
t _{STAH}	Start condition input hold time		3tcyc ⁽¹⁾	–	–	ns
t _{STAS}	Retransmit start condition input setup time		3tcyc ⁽¹⁾	–	–	ns
t _{STOP}	Stop condition input setup time		3tcyc ⁽¹⁾	–	–	ns
t _{SDAS}	Data input setup time		1tcyc + 40 ⁽¹⁾	–	–	ns
t _{SDAH}	Data input hold time		10	–	–	ns

Note:

1. 1tcyc = 1/f₁(s)

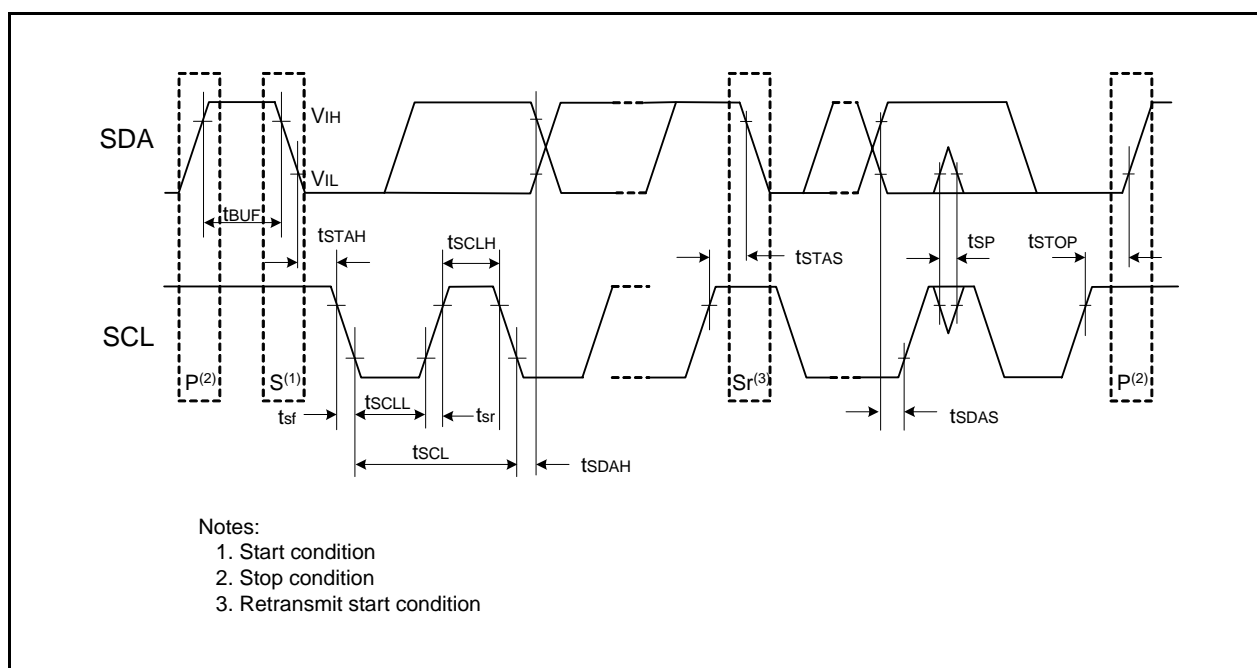


Figure 5.7 I/O Timing of I²C bus Interface

Table 5.26 Timing Requirements of External Clock Input (XIN, XCIN)
(V_{SS} = 0 V and T_{opr} = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Standard						Unit
		VCC = 2.2V, Topr = 25°C		VCC = 3V, Topr = 25°C		VCC = 5V, Topr = 25°C		
		Min.	Max.	Min.	Max.	Min.	Max.	
tC(XIN)	XIN input cycle time	200	—	50	—	50	—	ns
tWH(XIN)	XIN input “H” width	90	—	24	—	24	—	ns
tWL(XIN)	XIN input “L” width	90	—	24	—	24	—	ns
tC(XCIN)	XCIN input cycle time	20	—	20	—	20	—	μs
tWH(XCIN)	XCIN input “H” width	10	—	10	—	10	—	μs
tWL(XCIN)	XCIN input “L” width	10	—	10	—	10	—	μs

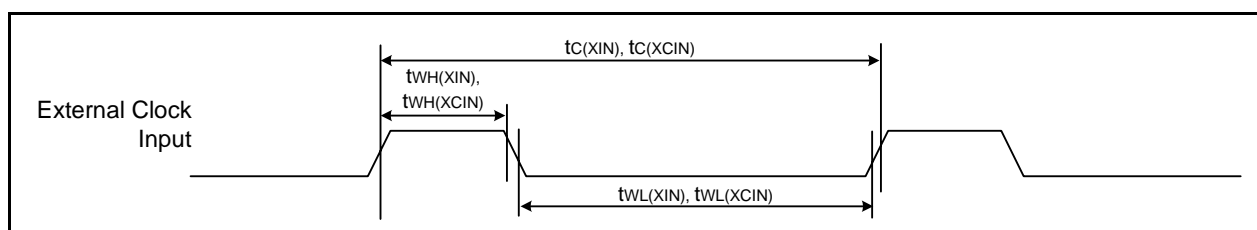


Figure 5.8 External Clock Input Timing

Table 5.27 Timing Requirements of TRJiIO (i = 0 or 1)
(V_{SS} = 0 V and T_{opr} = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Standard						Unit
		Vcc = 2.2V, Topr = 25°C		Vcc = 3V, Topr = 25°C		Vcc = 5V, Topr = 25°C		
		Min.	Max.	Min.	Max.	Min.	Max.	
t _c (TRJiO)	TRJiO input cycle time	500	—	300	—	100	—	ns
t _{WH} (TRJiO)	TRJiO input “H” width	200	—	120	—	40	—	ns
t _{WL} (TRJiO)	TRJiO input “L” width	200	—	120	—	40	—	ns

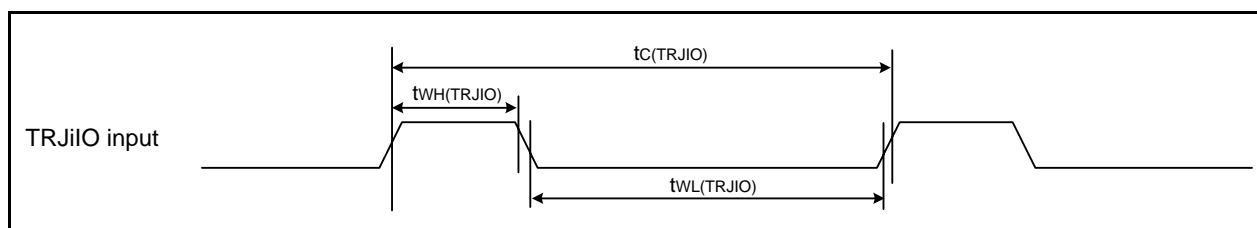


Figure 5.9 Input Timing of TRJiIO

Table 5.28 Timing Requirements of Serial Interface
($V_{SS} = 0\text{ V}$ and $T_{opr} = -20\text{ to }85\text{ }^{\circ}\text{C}$ (N version)/ $-40\text{ to }85\text{ }^{\circ}\text{C}$ (D version), unless otherwise specified.)

Symbol	Parameter	Standard						Unit
		Vcc = 2.2V, Topr = 25°C		Vcc = 3V, Topr = 25°C		Vcc = 5V, Topr = 25°C		
		Min.	Max.	Min.	Max.	Min.	Max.	
t _c (CK)	CLK0 input cycle time	800	—	300	—	200	—	ns
t _w (CKH)	CLK0 input “H” width	400	—	150	—	100	—	ns
t _w (CKL)	CLK0 input “L” width	400	—	150	—	100	—	ns
t _d (C-Q)	TXD0 output delay time	—	200	—	80	—	50	ns
t _h (C-Q)	TXD0 hold time	0	—	0	—	0	—	ns
t _{su} (D-C)	RXD0 input setup time	150	—	70	—	50	—	ns
t _h (C-D)	RXD0 input hold time	90	—	90	—	90	—	ns

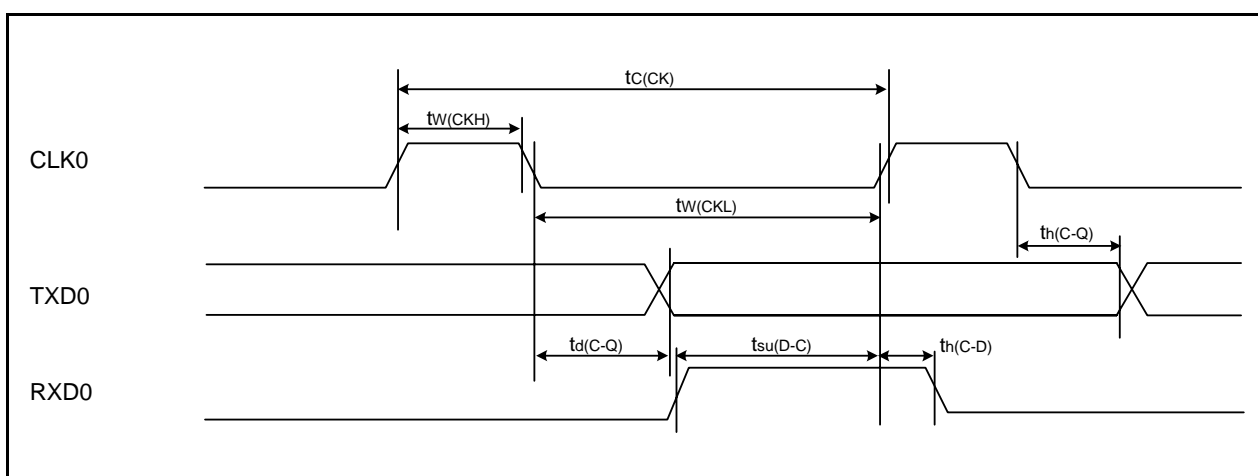


Figure 5.10 Input and Output Timing of Serial Interface

Table 5.29 Timing Requirements of External Interrupt $\overline{\text{INT}}i$ ($i = 0\text{ to }3, 5, 7$) and Key Input Interrupt $\overline{\text{KLI}}i$ ($i = 0\text{ to }7$)
($V_{SS} = 0\text{ V}$ and $T_{opr} = -20\text{ to }85\text{ }^{\circ}\text{C}$ (N version)/ $-40\text{ to }85\text{ }^{\circ}\text{C}$ (D version), unless otherwise specified.)

Symbol	Parameter	Standard						Unit
		Vcc = 2.2V, Topr = 25°C		Vcc = 3V, Topr = 25°C		Vcc = 5V, Topr = 25°C		
		Min.	Max.	Min.	Max.	Min.	Max.	
tw(INH)	$\overline{\text{INT}}i$ input "H" width, $\overline{\text{KLI}}i$ input "H" width	1000 ⁽¹⁾	—	380 ⁽¹⁾	—	250 ⁽¹⁾	—	ns
tw(INL)	$\overline{\text{INT}}i$ input "L" width, $\overline{\text{KLI}}i$ input "L" width	1000 ⁽²⁾	—	380 ⁽²⁾	—	250 ⁽²⁾	—	ns

Notes:

1. When selecting the digital filter by the $\overline{\text{INT}}i$ input filter select bit, use an $\overline{\text{INT}}i$ input HIGH width of either (1/digital filter clock frequency $\times 3$) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{\text{INT}}i$ input filter select bit, use an $\overline{\text{INT}}i$ input LOW width of either (1/digital filter clock frequency $\times 3$) or the minimum value of standard, whichever is greater.

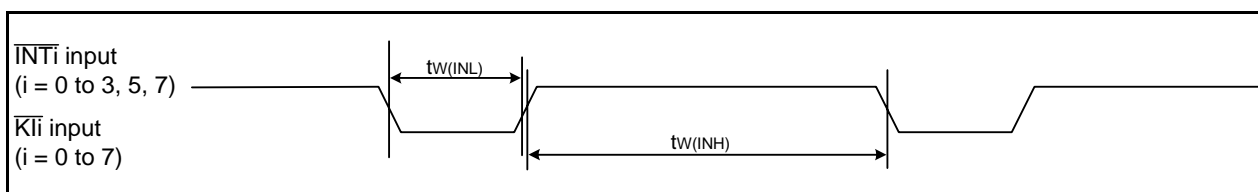


Figure 5.11 Input Timing of External Interrupt $\overline{\text{INT}}i$ and Key Input Interrupt $\overline{\text{KLI}}i$

Table 5.37 Flash Memory (Data flash Block A and Block B) Characteristics
(V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance ⁽¹⁾		10,000 (2)	–	–	times
–	Byte program time (program/erase endurance ≤ 10,000 times)		–	150	–	μs
–	Block erase time (program/erase endurance ≤ 10,000 times)	Internal ROM Capacity: 1 KB × 2	–	0.05	1	s
		Internal ROM Capacity: 2 KB × 2	–	0.055	1	s
t _d (SR-SUS)	Time delay from suspend request until suspend		–	–	0.25 + CPU clock × 3 cycles	ms
–	Time from suspend until erase restart		–	–	30 + CPU clock × 1 cycle	μs
t _d (CMDRST-READY)	Time from when command is forcibly terminated until reading is enabled		–	–	30 + CPU clock × 1 cycle	μs
–	Program, erase voltage		1.8	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20 (6)	–	85	°C
–	Data hold time ⁽⁷⁾	Ambient temperature = 85 °C	10	–	–	year

Notes:

- Definition of programming/erasure endurance
 The programming and erasure endurance is defined on a per-block basis.
 If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
 However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
- Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
- In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
- If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
- Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
- 40°C for D version.
- The data hold time includes time that the power supply is off or the clock is not supplied.

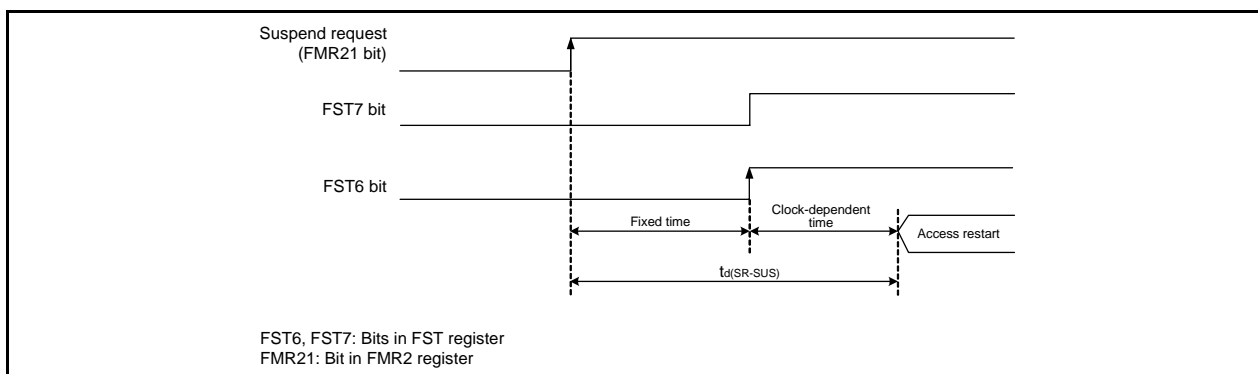


Figure 5.13 Time delay until Suspend

Table 5.38 Voltage Detection 0 Circuit Characteristics
(V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
V _{det0}	Voltage detection level V _{det0_0} ⁽¹⁾			1.8	1.90	2.05	V
	Voltage detection level V _{det0_1} ⁽¹⁾			2.15	2.35	2.50	V
	Voltage detection level V _{det0_2} ⁽¹⁾			2.70	2.85	3.05	V
	Voltage detection level V _{det0_3} ⁽¹⁾			3.55	3.80	4.05	V
—	Voltage detection 0 circuit response time ⁽³⁾	In operation	At the falling of V _{cc} from 5 V to (V _{det0_0} – 0.1) V	—	50	500	μs
		In stop mode	At the falling of V _{cc} from 5 V to (V _{det0_0} – 0.1) V	—	100	500	μs
—	Voltage detection circuit self power consumption	VCA25 = 1, V _{cc} = 5.0 V		—	1.5	—	μA
t _{d(E-A)}	Waiting time until voltage detection circuit operation starts ⁽²⁾			—	—	100	μs

Notes:

1. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
3. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.39 Voltage Detection 1 Circuit Characteristics
(V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Vdet1	Voltage detection level Vdet1_0 (1)	At the falling of Vcc		2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (1)	At the falling of Vcc		2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (1)	At the falling of Vcc		2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (1)	At the falling of Vcc		2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (1)	At the falling of Vcc		2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (1)	At the falling of Vcc		2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (1)	At the falling of Vcc		2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (1)	At the falling of Vcc		3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (1)	At the falling of Vcc		3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (1)	At the falling of Vcc		3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (1)	At the falling of Vcc		3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (1)	At the falling of Vcc		3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (1)	At the falling of Vcc		3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (1)	At the falling of Vcc		3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (1)	At the falling of Vcc		4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (1)	At the falling of Vcc		4.20	4.45	4.75	V
—	Hysteresis width at the rising of Vcc in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected		—	0.07	—	V
		Vdet1_6 to Vdet1_F selected		—	0.10	—	V
—	Voltage detection 1 circuit response time (2)	In operation	At the falling of Vcc from 5 V to (Vdet1_0 – 0.1) V	—	60	150	μs
		In stop mode	At the falling of Vcc from 5 V to (Vdet1_0 – 0.1) V	—	250	500	μs
—	Voltage detection circuit self power consumption	VCA26 = 1, Vcc = 5.0 V		—	1.7	—	μA
td(E-A)	Waiting time until voltage detection circuit operation starts (3)			—	—	100	μs

Notes:

1. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.45 LCD Drive Control Circuit Characteristics
(V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
VLCD	LCD power supply voltage	VLCD = VL3	2.2	–	5.5	V
VL2	VL2 voltage		VL1	–	VL3	V
VL1	VL1 voltage		1	–	VL2 (2)	V
f(FR)	Frame frequency		50	–	180	Hz
ILCD	LCD drive control circuit current		–	(1)	–	μA

Notes:

1. Refer to Table 5.48 DC Characteristics (2), Table 5.50 DC Characteristics (4), and Table 5.52 DC Characteristics (6).
2. The VL1 voltage should be VCC or below.

Table 5.46 Power-Off Mode Characteristics
(V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	Power-off mode operating supply voltage		1.8	–	5.5	V

Table 5.50 DC Characteristics (4) [2.7 V ≤ V_{CC} < 4.0 V]
(T_{OP} = −20 to 85°C (N version)/ −40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter		Condition							Standard			Unit
			Oscillation Circuit		On-Chip Oscillator		CPU Clock	Low-Power-Consumption Setting	Other	Min.	Typ. (3)	Max. .	
			XIN (2)	XCIN	High-Speed	Low-Speed							
I _{CC}	Power supply current ⁽¹⁾	High-speed clock mode	20 MHz	Off	Off	125 kHz	No division	—		—	4.7	10	mA
			10 MHz	Off	Off	125 kHz	No division	—		—	2.3	6	mA
			20 MHz	Off	Off	Off	No division	FMR27 = 1 MSTCR0 = BEh MSTCR1 = 3Fh	Flash memory off Program operation on RAM Module standby setting enabled	—	2.9	—	mA
			20 MHz	Off	Off	125 kHz	Divide-by-8	—		—	1.8	—	mA
			10 MHz	Off	Off	125 kHz	Divide-by-8	—		—	1.0	—	mA
		High-speed on-chip oscillator mode	Off	Off	20 MHz	125 kHz	No division	—		—	5.0	11	mA
			Off	Off	20 MHz	125 kHz	Divide-by-8	—		—	2.1	—	mA
			Off	Off	10 MHz	125 kHz	No division	—		—	2.9	—	mA
			Off	Off	10 MHz	125 kHz	Divide-by-8	—		—	1.5	—	mA
			Off	Off	4 MHz	125 kHz	Divide-by-16	MSTCR0 = BEh MSTCR1 = 3Fh		—	0.9	—	mA
		Low-speed on-chip oscillator mode	Off	Off	Off	125 kHz	No division	FMR27 = 1 VCA20 = 0		—	106	300	μA
			Off	Off	Off	125 kHz	Divide-by-8	FMR27 = 1 VCA20 = 0		—	54	200	μA
		Low-speed clock mode	Off	32 kHz	Off	Off	No division	FMR27 = 1 VCA20 = 0		—	54	200	μA
			Off	32 kHz	Off	Off	No division	FMSTP = 1 VCA20 = 0	Flash memory off Program operation on RAM	—	36	—	μA
		Wait mode	Off	Off	Off	125 kHz	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1	While a WAIT instruction is executed Peripheral clock operation	—	9.0	50	μA
			Off	Off	Off	125 kHz	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off	—	2.5	31	μA
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 0	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode	—	3.1	—	μA
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode	—	1.7	—	μA
			Off	32 kHz	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	While a WAIT instruction is executed Peripheral clock off	—	0.5	2.2	μA
		Stop mode	Off	Off	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 0 Topr = 25°C	—	0.01	0.1	μA
			Off	Off	Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 0 Topr = 85°C	—	0.02	—	μA
		Power-off mode	Off	Off	Off	Off	—	—	Power-off 0 Topr = 25°C	—	0.01	0.1	μA
			Off	Off	Off	Off	—	—	Power-off 0 Topr = 85°C	—	0.02	—	μA
Off	32 kHz		Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 25°C	—	1.3	4.5	μA		
Off	32 kHz		Off	Off	—	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 85°C	—	2.2	—	μA		

Notes:

1. V_{CC} = 2.7 V to 4.0 V, single chip mode, output pins are open, and other pins are V_{SS}.
2. XIN is set to square wave input.
3. V_{CC} = 3.0 V
4. VLCD = V_{CC}, external division resistors are used for VL3 to VL1, 1/3 bias, 1/4 duty, f(FR) = 64 Hz, SEG0 to SEG39 are selected, and segment and common output pins are open. The standard value does not include the current that flows through external division resistors.

